

Electronic supplementary information

All-Inorganic Quantum-Dot Light-Emitting Devices Formed via Low-Cost, Wet-Chemical Processing

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Atomic force microscope (AFM) scans were performed on bare ITO substrates (Fig. S1) and on NiO films deposited on clean Si wafer substrates (Fig. S2). These results were compared with measured RMS roughness value of 1.4 nm that was obtained for NiO films deposited onto ITO substrates. The bare ITO substrate gave a RMS roughness value of 2.6 nm. The Si/NiO sample gave a RMS roughness value of 0.6 nm. These data indicate the spin-coated NiO material forms a very smooth surface and that the observed roughness of the ITO/NiO sample can be attributed to the underlying ITO topology.

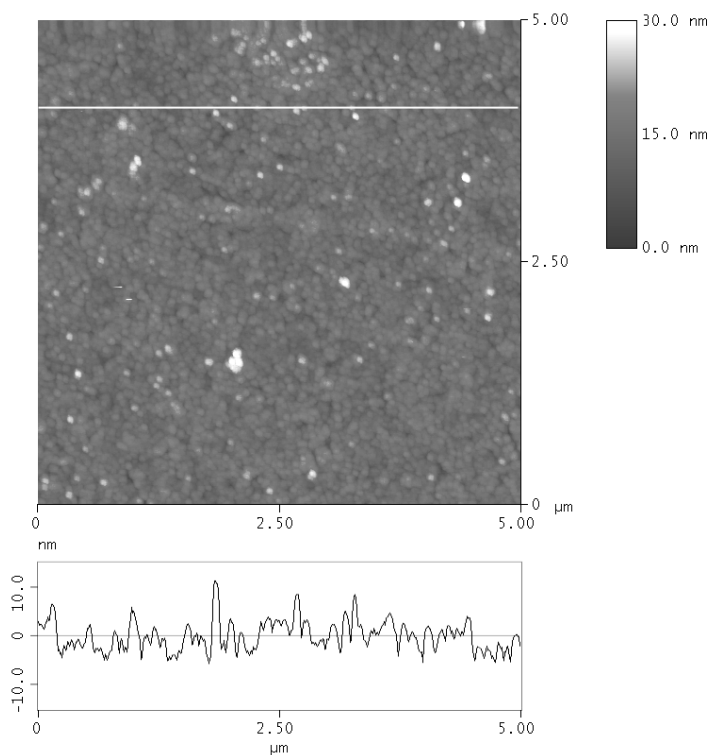


Fig. S1 Tapping mode AFM scans and line analysis of cleaned ITO substrate.

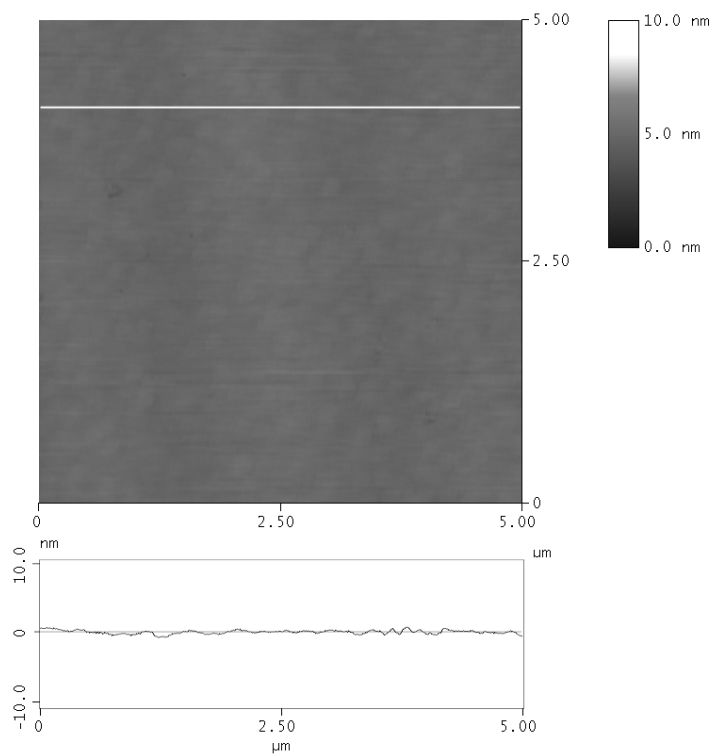


Fig. S2 Tapping mode AFM scans and line analysis of 40 nm thick sol-gel derived NiO film deposited on Si wafer.